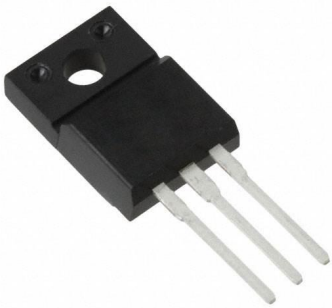


2SB0942AP Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	2SB0942AP-DG
Manufacturer	Panasonic Electronic Components
Manufacturer Product Number	2SB0942AP
Description	TRANS PNP 80V 4A TO220F-A1
Detailed Description	Bipolar (BJT) Transistor PNP 80 V 4 A 30MHz 2 W Th rough Hole TO-220F-A1



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

2SB0942AP

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

80 V

Current - Collector Cutoff (Max):

700µA

Power - Max:

2 W

Operating Temperature:

150°C (TJ)

Package / Case:

TO-220-3 Full Pack

Base Product Number:

2SB094

Manufacturer:

Panasonic Electronic Components

Product Status:

Obsolete

Current - Collector (Ic) (Max):

4 A

Vce Saturation (Max) @ Ib, Ic:

1.5V @ 400mA, 4A

DC Current Gain (hFE) (Min) @ Ic, Vce:

120 @ 1A, 4V

Frequency - Transition:

30MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-220F-A1

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

HTSUS:

8541.29.0075

ECCN:

EAR99

2SB0942 (2SB942), 2SB0942A (2SB942A)

Silicon PNP epitaxial planar type

For low-frequency power amplification

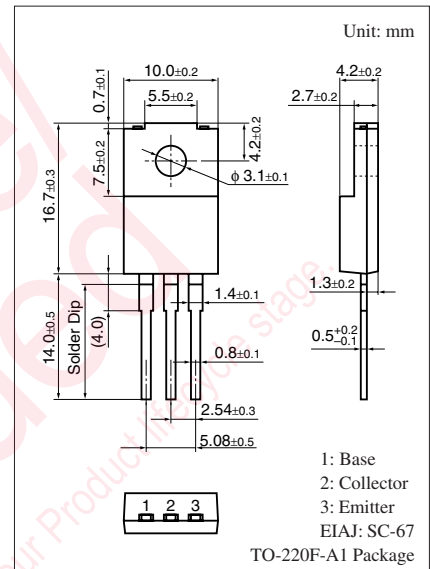
Complementary to 2SD1267, 2SD1267A

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Large collector-emitter saturation voltage $V_{CE(sat)}$
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0942	-60	V
	2SB0942A	-80	
Collector-emitter voltage (Base open)	2SB0942	-60	V
	2SB0942A	-80	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-4	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	$T_a = 25^\circ\text{C}$	P_C	40
			2
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

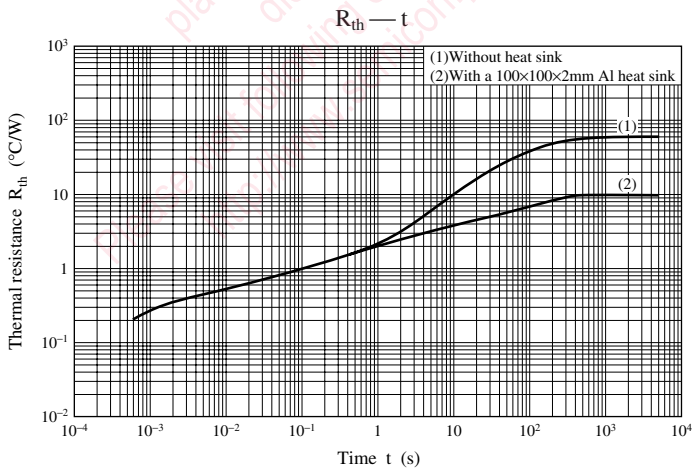
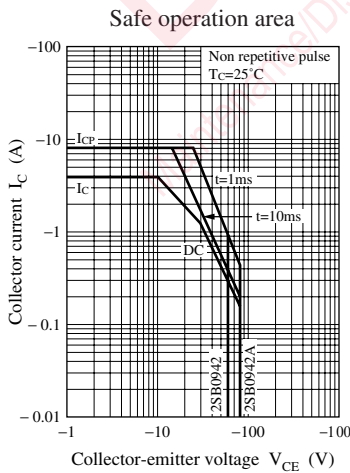
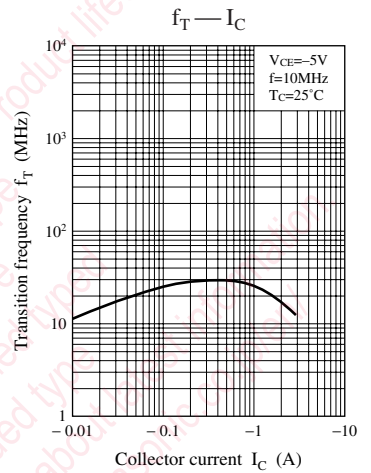
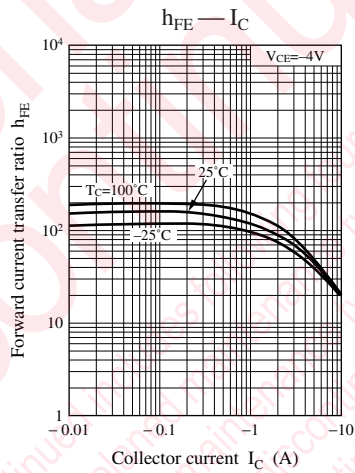
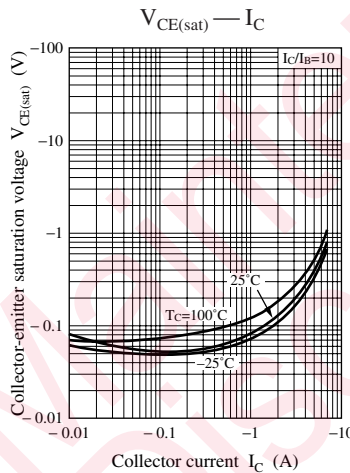
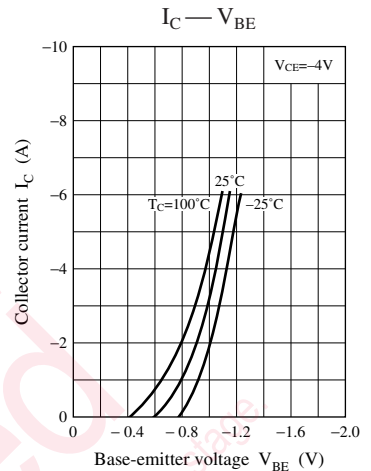
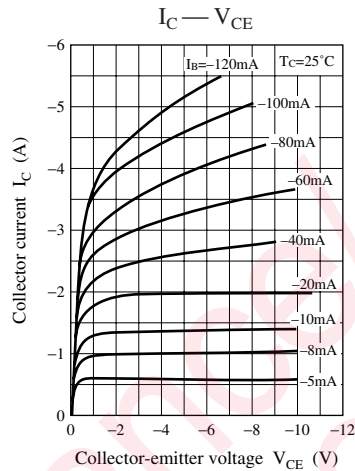
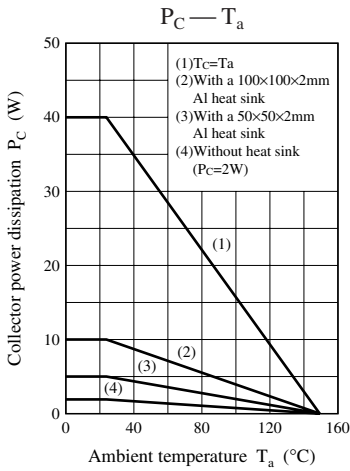
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0942	$I_C = -30 \text{ mA}, I_B = 0$	-60			V
	2SB0942A		-80			
Base-emitter voltage	V_{BE}	$V_{CE} = -4 \text{ V}, I_C = -3 \text{ A}$			-2	V
Collector-emitter cutoff current (E-B short)	2SB0942	$V_{CE} = -60 \text{ V}, V_{BE} = 0$			-400	μA
	2SB0942A		$V_{CE} = -80 \text{ V}, V_{BE} = 0$		-400	
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -30 \text{ V}, I_B = 0$			-700	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -4 \text{ V}, I_C = -1 \text{ A}$	40		250	—
	h_{FE2}	$V_{CE} = -4 \text{ V}, I_C = -3 \text{ A}$	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4 \text{ A}, I_B = -0.4 \text{ A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -0.1 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -4 \text{ A}, I_{B1} = -0.4 \text{ A}, I_{B2} = 0.4 \text{ A}$		0.2		μs
Storage time	t_{stg}	$V_{CC} = -50 \text{ V}$		0.5		μs
Fall time	t_f			0.2		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	Q	P
h_{FE1}	40 to 90	70 to 150	120 to 250

Note) The part numbers in the parenthesis show conventional part number.



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